

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



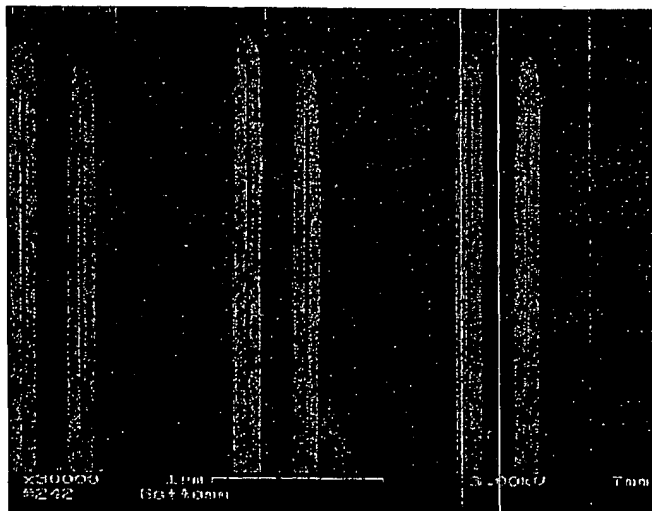
(43) International Publication Date
22 January 2004 (22.01.2004)

PCT

(10) International Publication Number
WO 2004/007796 A1

- (51) International Patent Classification⁷: **C23C 16/34**,
C07F 11/00, H01L 21/768, 21/02
- (21) International Application Number:
PCT/US2003/021281
- (22) International Filing Date: 9 July 2003 (09.07.2003)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
60/395,572 12 July 2002 (12.07.2002) US
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- (54) Title: **VAPOR DEPOSITION OF TUNGSTEN NITRIDE**
- (84) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).
- Published:
— with international search report
— before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

[Continued on next page]



(57) Abstract: Tungsten nitride films were deposited on heated substrates by the reaction of vapors of tungsten bis(alkylimide)bis(dimethylamide) and a Lewis base or a hydrogen plasma. For example, vapors of tungsten bis(*tert*-butylimide)bis(dimethylamide) and ammonia gas supplied in alternate doses to surfaces heated to 300 °C produced coatings of tungsten nitride having very uniform thickness and excellent step coverage in holes with aspect ratios up to at least 40:1. The films are metallic and good electrical conductors. Suitable applications in microelectronics include barriers to the diffusion of copper and electrodes for capacitors. Similar processes deposit molybdenum nitride, which is suitable for layers alternating with silicon in X-ray mirrors.

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